P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)[c]	Q_g (Typ.)
- 100	0.138 at V_{GS} = - 10 V	- 16.3	24 nC
	0.141 at V_{GS} = - 7.5 V	- 16.1	
	0.142 at V_{GS} = - 6 V	- 16.1	

FEATURES

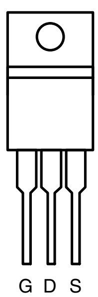
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Material categorization:
  For definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

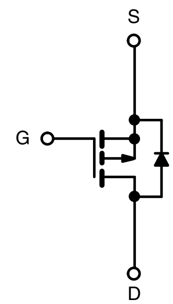
- DC/DC Converters
- Motor Control

TO-220AB



Drain connected to Tab

Top View



P-Channel MOSFET

Ordering Information:
SUP25P10-138-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 16.3	A
	T_C = 125 °C		- 7.3	
Pulsed Drain Current (t = 100 µs)		I_{DM}	- 40	
Avalanche Current	L = 0.1 mH	I_{AS}	- 25	
Single Pulse Avalanche Energy[a]		E_{AS}	31.25	mJ
Power Dissipation	T_C = 25 °C	P_D	73.5[b]	W
	T_A = 25 °C		3.1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient Free Air	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	1.7	

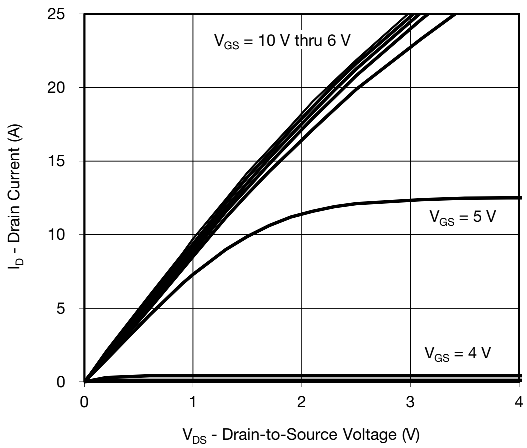
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. T_C = 25 °C

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250 µA	- 2		- 4	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 105		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = - 250 µA		6.6		
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 100 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 100 V, V_{GS} = 0 V, T_J = 125 °C			- 50	
		V_{DS} = - 100 V, V_{GS} = 0 V, T_J = 150 °C			- 200	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 10 V	- 20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 6 A		0.115	0.138	Ω
		V_{GS} = - 7.5 V, I_D = - 6 A		0.117	0.141	
		V_{GS} = - 6 V, I_D = - 6 A		0.118	0.142	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 6 A		18		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 50 V, f = 1 MHz		2110		pF
Output Capacitance	C_{oss}			105		
Reverse Transfer Capacitance	C_{rss}			58		
Total Gate Charge[c]	Q_g	V_{DS} = - 50 V, V_{GS} = - 10 V, I_D = - 6.7 A		40	60	nC
		V_{DS} = - 50 V, V_{GS} = - 6 V, I_D = - 6.7 A		24	36	
Gate-Source Charge[c]	Q_{gs}			12.5		
Gate-Drain Charge[c]	Q_{gd}			6.7		
Gate Resistance	R_g	f = 1 MHz	2	8	16	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 50 V, R_L = 10 Ω I_D ≅ - 5 A, V_{GEN} = - 10 V, R_g = 1 Ω		7	14	ns
Rise Time[c]	t_r			12	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			46	70	
Fall Time[c]	t_f			40	60	
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 50 V, R_L = 10 Ω I_D ≅ - 5 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		12	20	
Rise Time[c]	t_r			105	160	
Turn-Off Delay Time[c]	$t_{d(off)}$			36	54	
Fall Time[c]	t_f			34	51	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				- 16.3	A
Pulsed Current (t = 100 µs)	I_{SM}				- 40	
Forward Voltage[a]	V_{SD}	I_F = - 5 A, V_{GS} = 0 V		- 0.85	- 1.5	V
Reverse Recovery Time	t_{rr}	I_F = - 5 A, dI/dt = 100 A/µs		70	105	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			- 7	- 14	A
Reverse Recovery Charge	Q_{rr}			220	330	nC

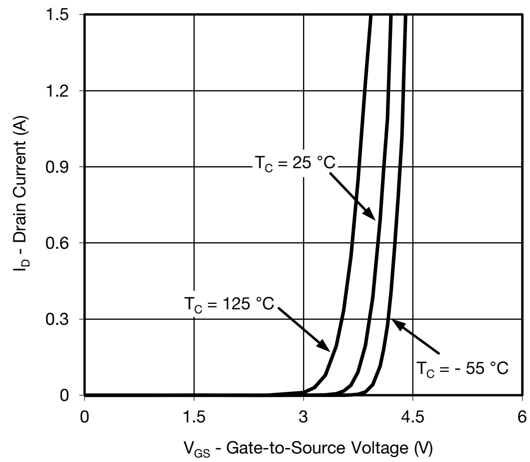
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

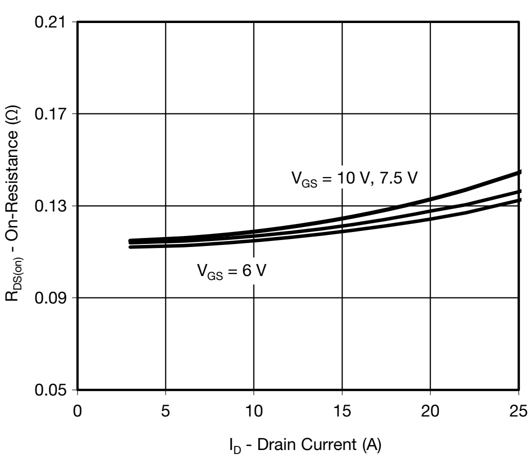
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



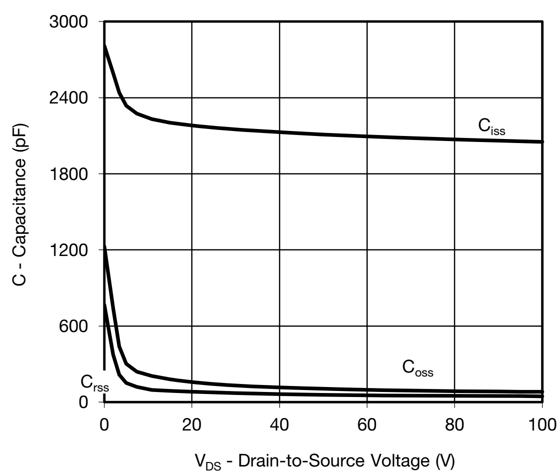
Output Characteristics



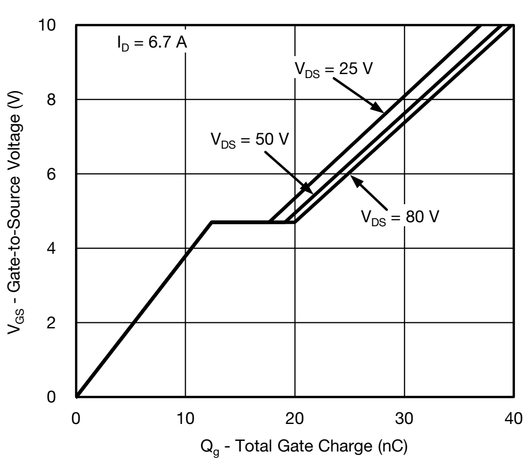
Transfer Characteristics



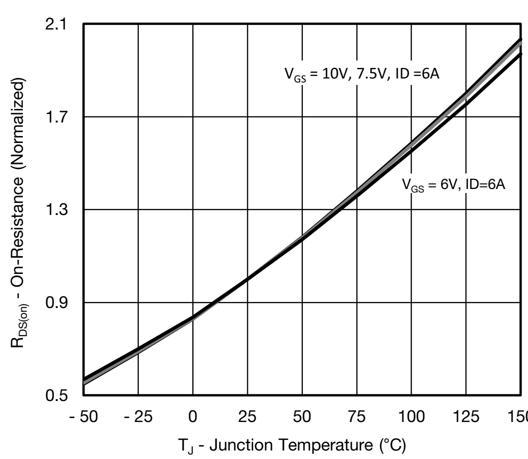
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

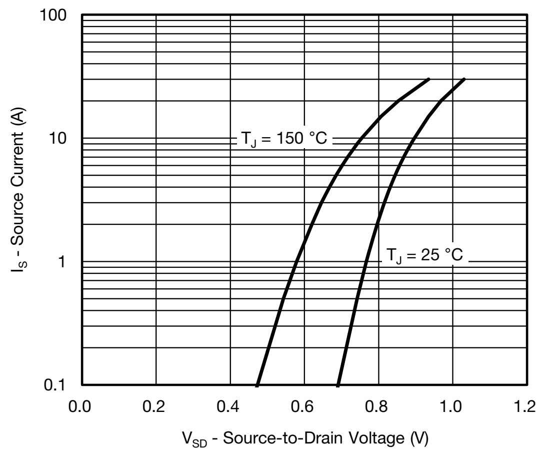


Gate Charge

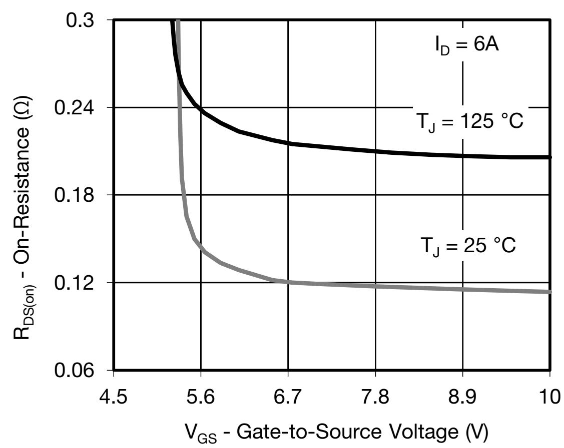


On-Resistance vs. Junction Temperature

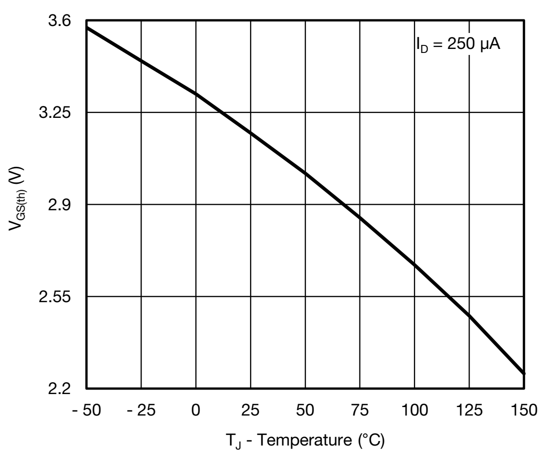
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



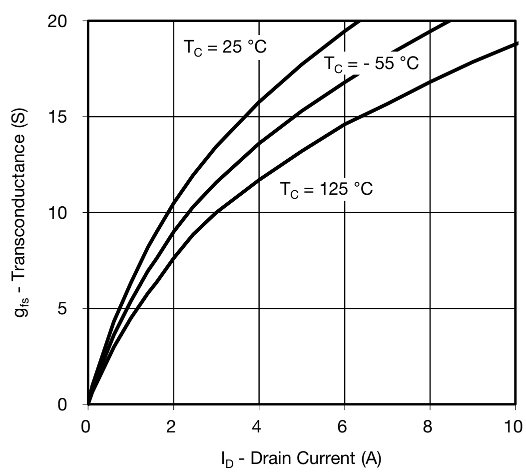
Source-Drain Diode Forward Voltage



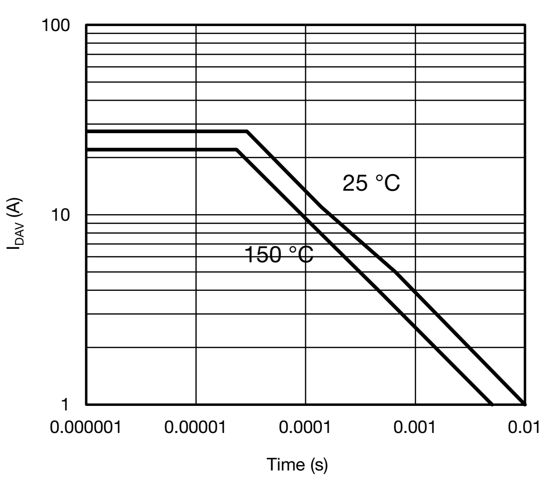
On-Resistance vs. Gate-to-Source Voltage



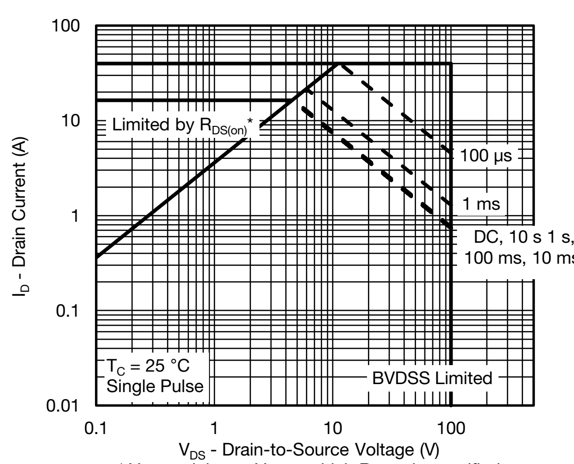
Threshold Voltage



Transconductance



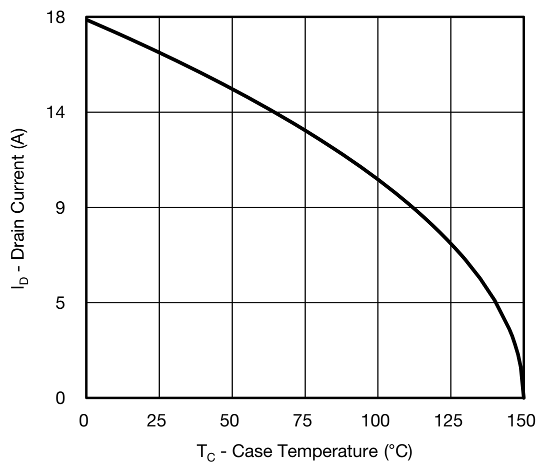
Single Pulse Avalanche Capability



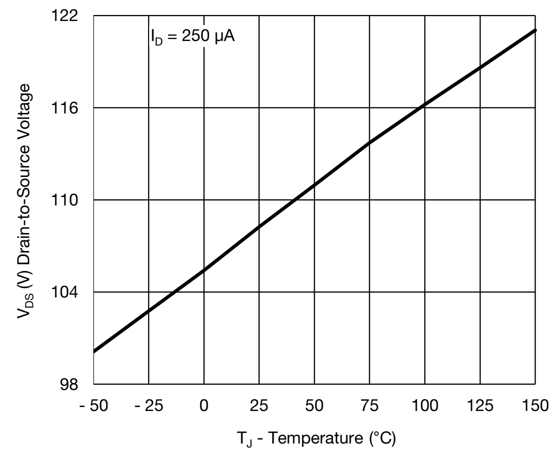
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

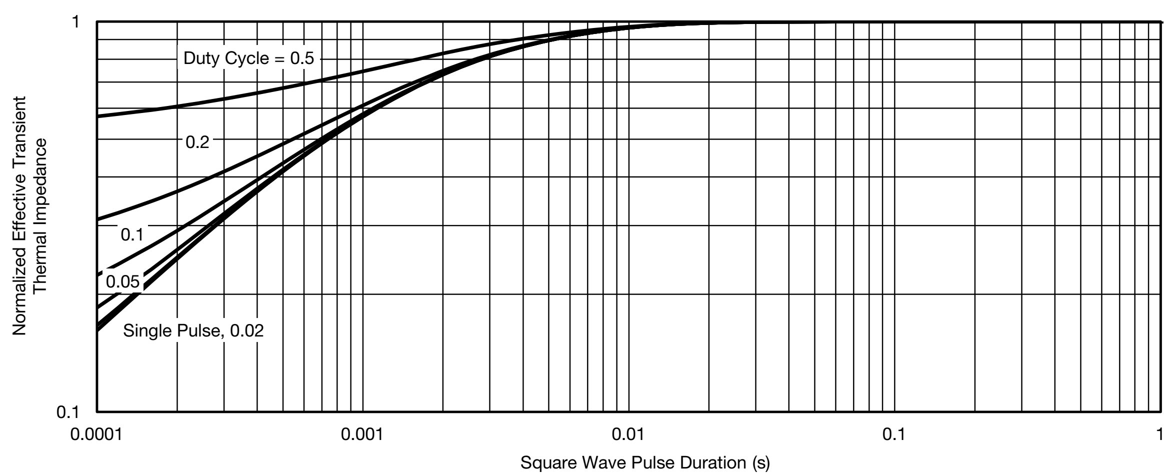


Current Derating*



Drain Source Breakdown vs. Junction Temperature

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



Normalized Thermal Transient Impedance, Junction-to-Case

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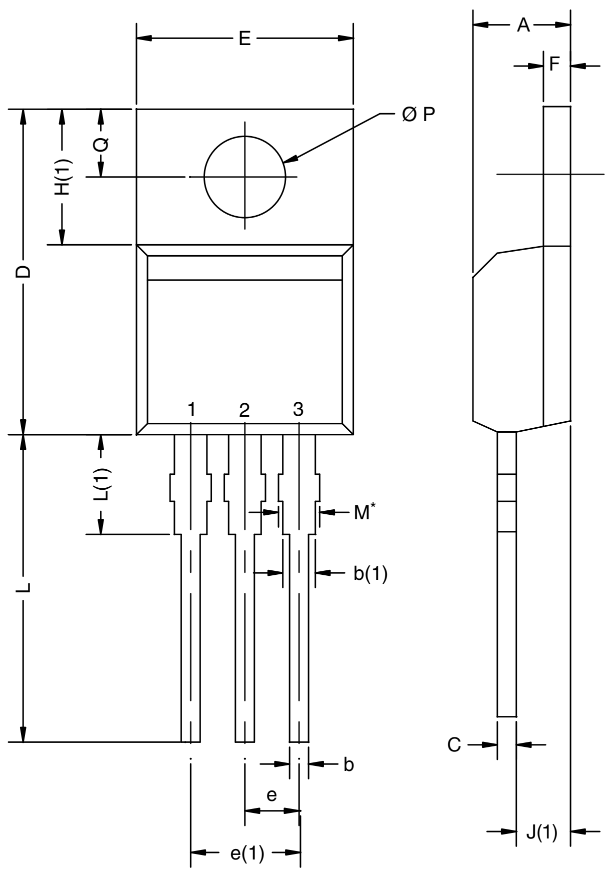
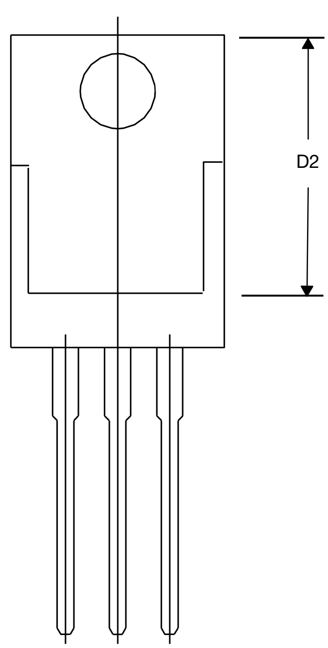


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM



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